

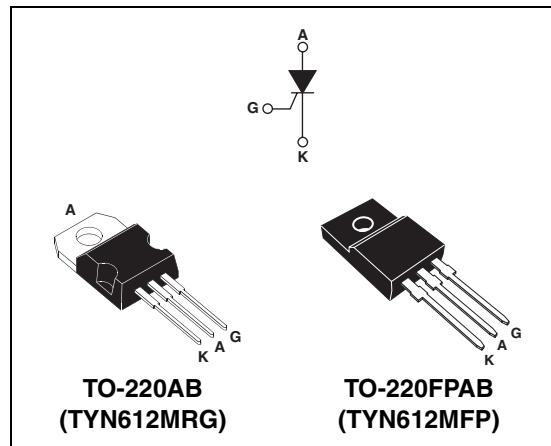
**Table 1: Main Features**

Symbol	Value	Unit
$I_T(\text{RMS})$	12	A
$V_{\text{DRM}}/V_{\text{RRM}}$	600	V
$I_{\text{GT}}$ (min./max.)	1.5 / 5	mA

**DESCRIPTION**

The TYN612M SCR is suitable to fit modes of control found in applications such as voltage regulation circuits for motorbikes, overvoltage crowbar protection, motor control circuits in power tools and kitchen aids, inrush current limiting circuits, capacitive discharge ignition.

The insulated fullpack package allows a back to back configuration.


**Table 2: Order Codes**

Part Number	Marking
TYN612MRG	TYN612M
TYN612MFP	TYN612MFP

**Table 3: Absolute Ratings (limiting values)**

Symbol	Parameter		Value	Unit
$I_T(\text{RMS})$	RMS on-state current (180° conduction angle)	TO-220AB	$T_c = 105^\circ\text{C}$	12
		TO-220FPAB	$T_c = 70^\circ\text{C}$	12
$I_T(\text{AV})$	Average on-state current (180° conduction angle)	TO-220AB	$T_c = 105^\circ\text{C}$	8
		TO-220FPAB	$T_c = 70^\circ\text{C}$	8
$I_{\text{TSM}}$	Non repetitive surge peak on-state current	$t_p = 8.3 \text{ ms}$	$T_j = 25^\circ\text{C}$	125
		$t_p = 10 \text{ ms}$		120
$I^2t$	$I^2t$ Value for fusing	$t_p = 10 \text{ ms}$	$T_j = 25^\circ\text{C}$	$\text{A}^2\text{s}$
$dI/dt$	Critical rate of rise of on-state current $I_G = 2 \times I_{\text{GT}}$ , $t_r \leq 100 \text{ ns}$	$F = 60 \text{ Hz}$	$T_j = 125^\circ\text{C}$	$\text{A}/\mu\text{s}$
$I_{\text{GM}}$	Peak gate current	$t_p = 20 \mu\text{s}$	$T_j = 125^\circ\text{C}$	A
$P_{\text{G(AV)}}$	Average gate power dissipation		$T_j = 125^\circ\text{C}$	1
$T_{\text{stg}}$ $T_j$	Storage junction temperature range Operating junction temperature range		- 40 to + 150	$^\circ\text{C}$
			- 40 to + 125	
$V_{\text{RGM}}$	Maximum peak reverse gate voltage		5	V

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**Tables 4: Electrical Characteristics ( $T_j = 25^\circ\text{C}$ , unless otherwise specified)**

Symbol	Test Conditions		Value	Unit
$I_{GT}$	$V_D = 12 \text{ V}$ $R_L = 140 \Omega$		MIN.	1.5
			MAX.	5
$V_{GT}$			MAX.	1.3
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$	$T_j = 125^\circ\text{C}$	MIN.	0.2
$I_H$	$I_T = 500 \text{ mA}$ Gate open		MAX.	20
$I_L$	$I_G = 1.2 I_{GT}$		MAX.	40
$dV/dt$	$V_D = 67 \% V_{DRM}$ Gate open	$T_j = 125^\circ\text{C}$	MIN.	50
$V_{TM}$	$I_{TM} = 24 \text{ A}$ $t_p = 380 \mu\text{s}$	$T_j = 25^\circ\text{C}$	MAX.	1.6
$V_{t0}$	Threshold voltage	$T_j = 125^\circ\text{C}$	MAX.	0.85
$R_d$	Dynamic resistance	$T_j = 125^\circ\text{C}$	MAX.	30
$I_{DRM}$	$V_{DRM} = V_{RRM}$	$T_j = 25^\circ\text{C}$	MAX.	5
		$T_j = 125^\circ\text{C}$		2
				mA

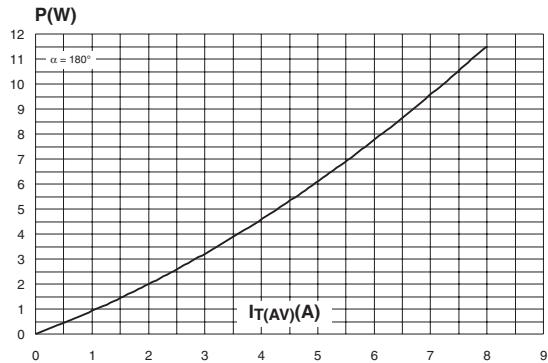
**Table 5: Thermal Resistances**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case (DC)	TO-220AB	1.3
		TO-220FPAB	4.5
$R_{th(j-a)}$	Junction to ambient	TO-220AB	55
		TO-220FPAB	55
			°C/W

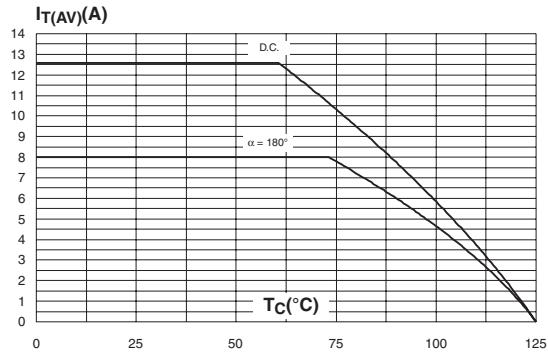
**Table 6: Product Selector**

Part Number	Voltage	Sensitivity	Package
TYN612MRG	600V	5mA	TO-220AB
TYN612MFP	600V	5mA	TO-220FPAB

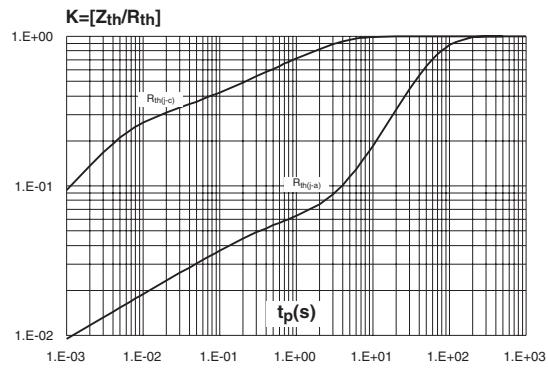
**Figure 1: Maximum average power dissipation versus average on-state current**



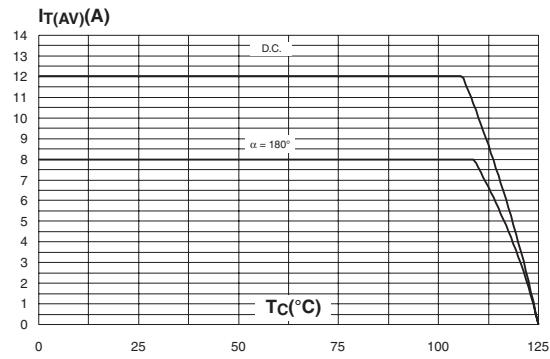
**Figure 3: Average and D.C. on-state current versus case temperature (TO-220FPAB)**



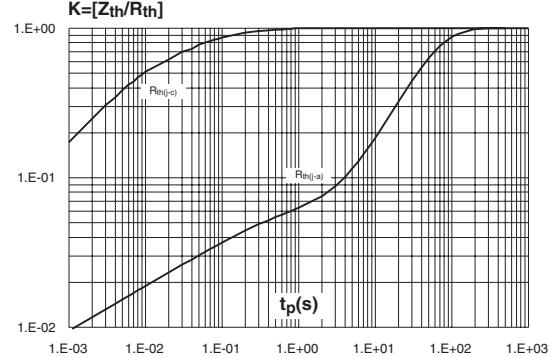
**Figure 5: Relative variation of thermal impedance versus pulse duration (TO-220FPAB)**



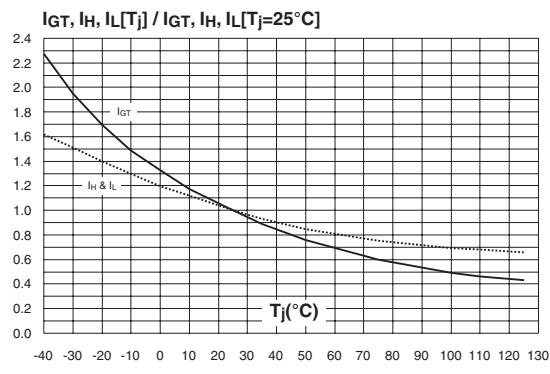
**Figure 2: Average and D.C. on-state current versus case temperature (TO-220AB)**



**Figure 4: Relative variation of thermal impedance versus pulse duration (TO-220AB)**

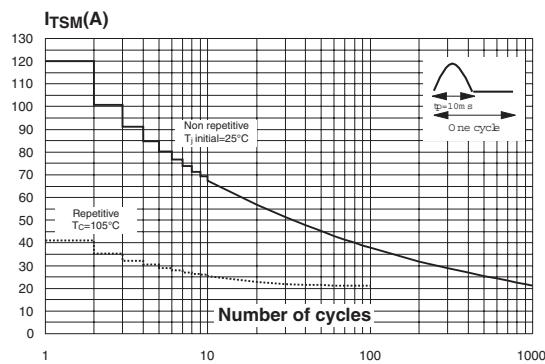


**Figure 6: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values)**

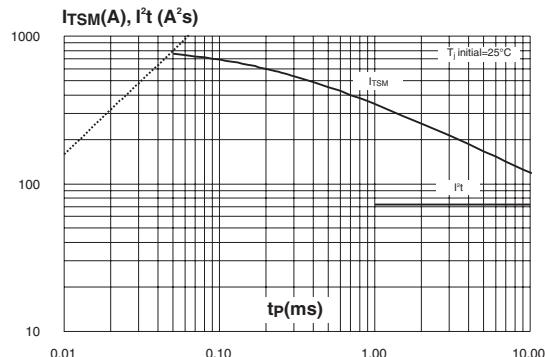


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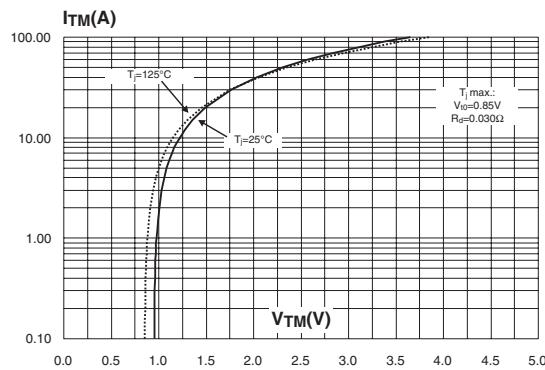
**Figure 7: Surge peak on-state current versus number of cycles**



**Figure 8: Non repetitive surge peak on-state current for a sinusoidal pulse with width  $tp < 10ms$ , and corresponding value of  $I^2t$**



**Figure 9: On-state characteristics (maximum values)**



**Figure 10: Ordering Information Scheme**

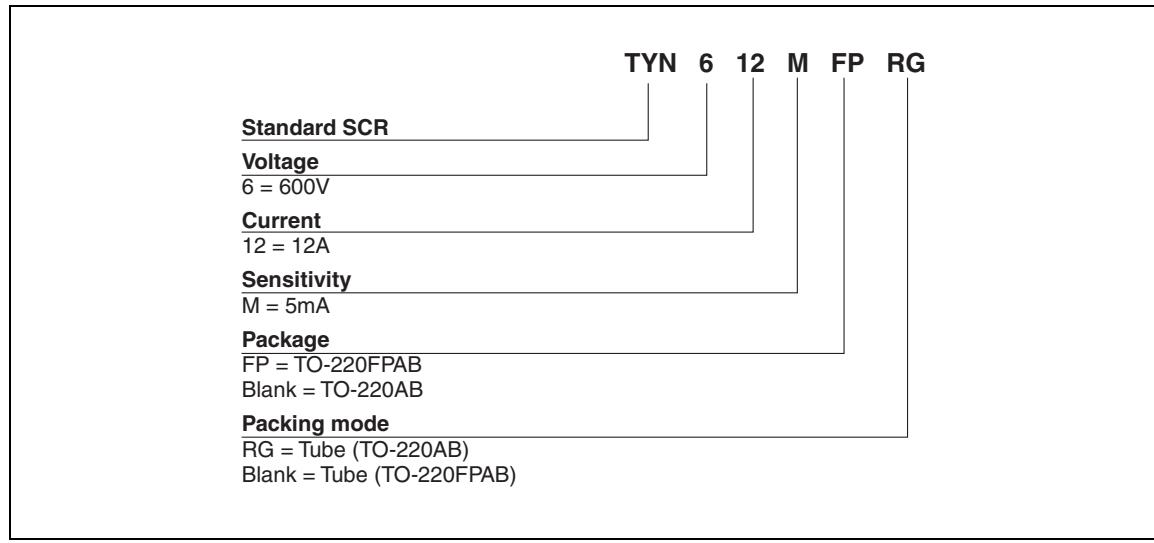
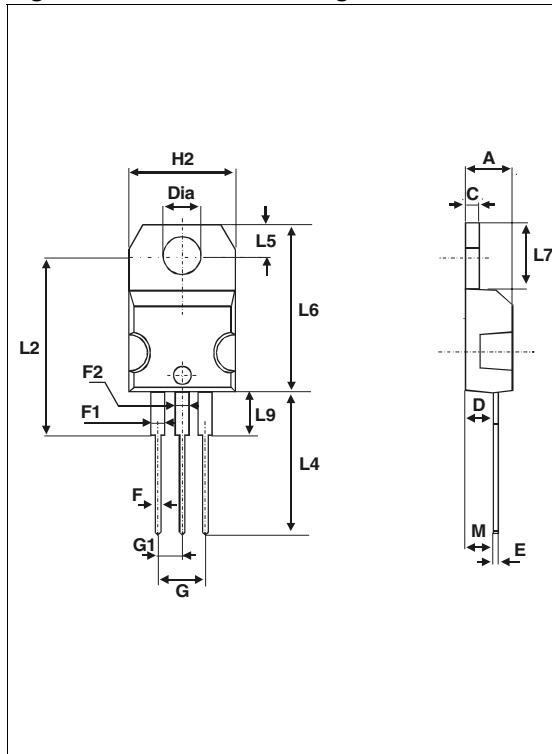
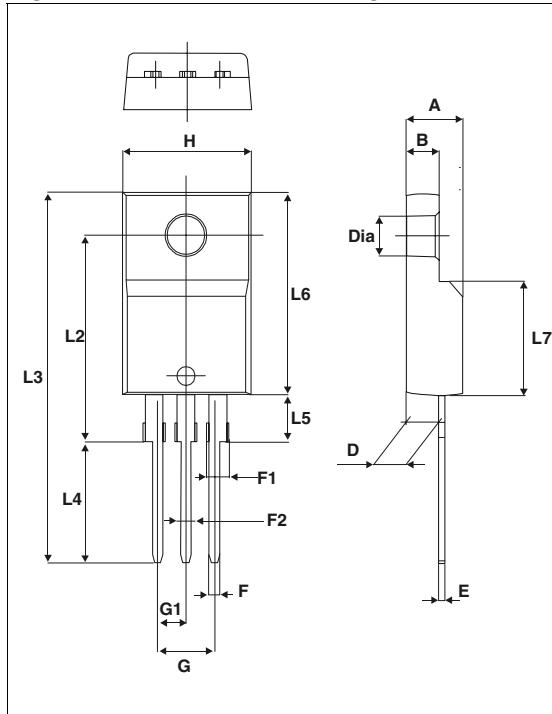


Figure 11: TO-220AB Package Mechanical Data



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 typ.		0.645 typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam.	3.75	3.85	0.147	0.151

Figure 12: TO-220FPAB Package Mechanical Data



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.4	4.6	0.173	0.181
B	2.5	2.7	0.098	0.106
D	2.5	2.75	0.098	0.108
E	0.45	0.70	0.018	0.027
F	0.75	1	0.030	0.039
F1	1.15	1.70	0.045	0.067
F2	1.15	1.70	0.045	0.067
G	4.95	5.20	0.195	0.205
G1	2.4	2.7	0.094	0.106
H	10	10.4	0.393	0.409
L2	16 Typ.		0.63 Typ.	
L3	28.6	30.6	1.126	1.205
L4	9.8	10.6	0.386	0.417
L5	2.9	3.6	0.114	0.142
L6	15.9	16.4	0.626	0.646
L7	9.00	9.30	0.354	0.366
Dia.	3.00	3.20	0.118	0.126

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**Table 7: Ordering Information**

<b>Ordering type</b>	<b>Marking</b>	<b>Package</b>	<b>Weight</b>	<b>Base qty</b>	<b>Delivery mode</b>
TYN612MRG	TYN612M	TO-220AB	2.3 g	50	Tube
TYN612MFP	TYN612MFP	TO-220FPAB	2 g	50	Tube

**Table 8: Revision History**

<b>Date</b>	<b>Revision</b>	<b>Description of Changes</b>
Sep-2002	1A	Last update.
10-Feb-2005	2	TO-220FPAB package added.

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